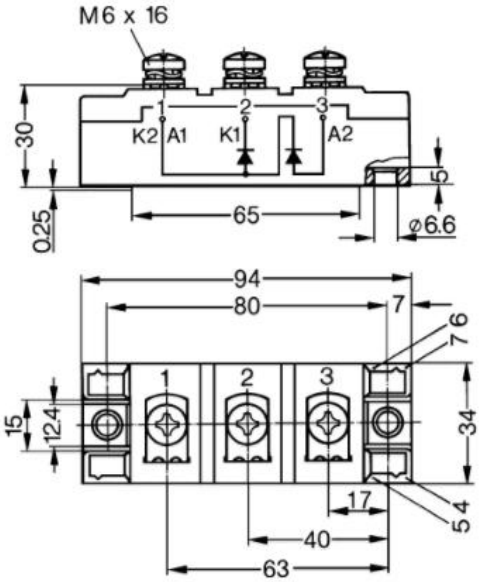
CD610816C

Dual Diode Isolated Module

FEATURES

- Electrically Isolated Heatsinking
- Metal Baseplate
- Low Thermal Impedance For Improved Current Capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Power supplies
- Bridge Circuits
- AC/DC Motor Drives

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_R	Repetitive Peak Reverse Voltage		800	V
$I_{F(AV)}$	Average Forward Current	180° conduction,T_C=100℃	160	A
I_{FSM}	Non-Repetitive, Peak On Cycle Surge Forward Current	60Hz,100% V_{RRM} reapplied, T_J=150℃	3500	A
		60Hz,No V_{RRM} reapplied,T_J=150℃	4200	
		50Hz,100% V_{RRM} reapplied,T_J=150℃	3350	
		50Hz,No V_{RRM} reapplied,T_J=150℃	4000	
Viso	Isolated Voltage	T_C=25℃, 1sec	2500	V
T_J	Junction Temperature		-40~150	℃
T_{stg}	Storage Temperature Range		-40~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	Per module,both conducting	0.1	℃/W
		Per junction,both conducting	0.2	

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Forward Voltage drop	I_F= 520A, 180° conduction	1.43	V
I_R	Instantaneous Reverse Current	V_R=800V, T_J= 150℃	20	mA